

SOT-23 Plastic-Encapsulate Transistors

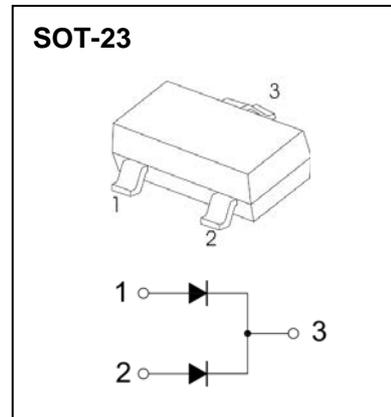
RB495D SCHOTTKY BARRIER DIODE

FEATURES

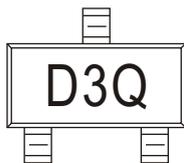
- Small Surface Mounting Type
- Low Forward Voltage
- Low Reverse Current
- High Reliability

APPLICATIONS

- General Rectification



MARKING: D3Q



D3Q = Device code

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RRM}	Peak Repetitive Reverse Voltage	40	V
V_{RWM}	Working Peak Reverse Voltage		
$V_{R(RMS)}$	RMS Reverse Voltage	28	V
I_o	Continuous Forward Current	400	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current@ $t=8.3\text{ms}$	2	A
P_D	Power Dissipation	250	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	400	$^{\circ}\text{C}/\text{W}$
T_J	Operating Junction Temperature Range	-40 ~ +125	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55 ~ +150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	25			V
Reverse current	I_R	$V_R=25\text{V}$			70	μA
Forward voltage	V_F	$I_F=10\text{mA}$			0.3	V
		$I_F=200\text{mA}$			0.5	

Typical Characteristics
